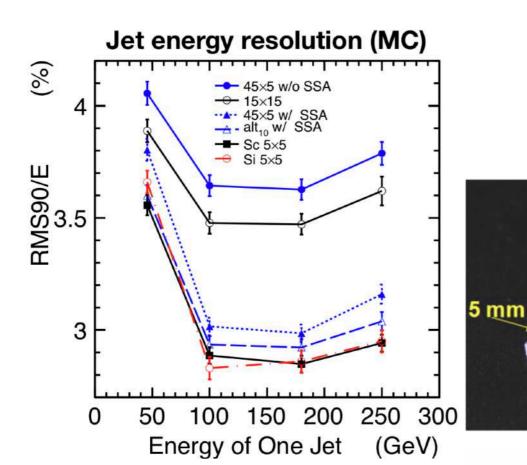
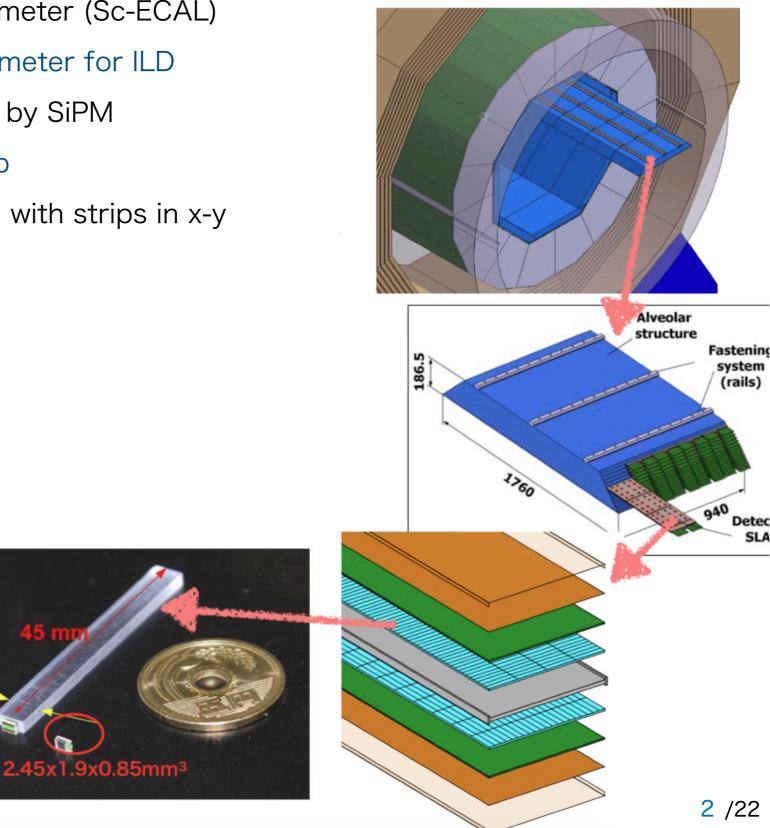
Study on Saturation of SiPM using UV laser

Naoki Tsuji, The University of Tokyo Linghui Liu, Wataru Ootani, Kosuke Yoshioka, Makoto Gonokami, Yusuke Morita LCWS2019 at Sendai, 28/Oct./2019 - 1/Nov./2019

Sc-ECAL

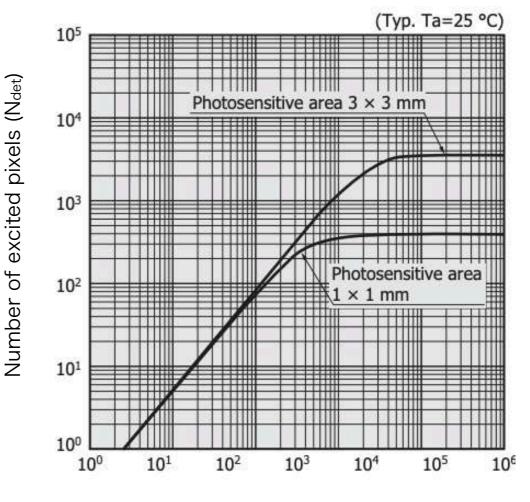
- Scintillator Electromagnetic CALorimeter (Sc-ECAL)
 - Technology option of EM calorimeter for ILD
- Based on scintillator strips readout by SiPM
 - 5 × 45 × 2 mm³ scintillator strip
- Virtual segmentation : 5mm × 5mm with strips in x-y configuration
- Timing resolution < 1 ns</p>
- Low cost





Saturation of SiPMs

- SiPM saturation can be an issue for Sc-ECAL
 - To measure small and dense EM shower
 - Pile-up hits in small and dense EM shower
 - When a large number of photons are injected to SiPM, output of SiPM can be saturated due to limited number of pixels
- Saturation curve is usually measured by direct injecting fast laser pulse (~400 nm) to SiPM
 - Time constant of emission of scintillation light (few ns) is not negligible compared to recovery time of SiPM cell (dozens ns)
- Our idea is to measure the SiPM saturation with scintillation light excited by UV pulse laser
 - The measured saturation curve can directly be used for saturation correction in Sc-ECAL



Number of incident photons (Nseed)

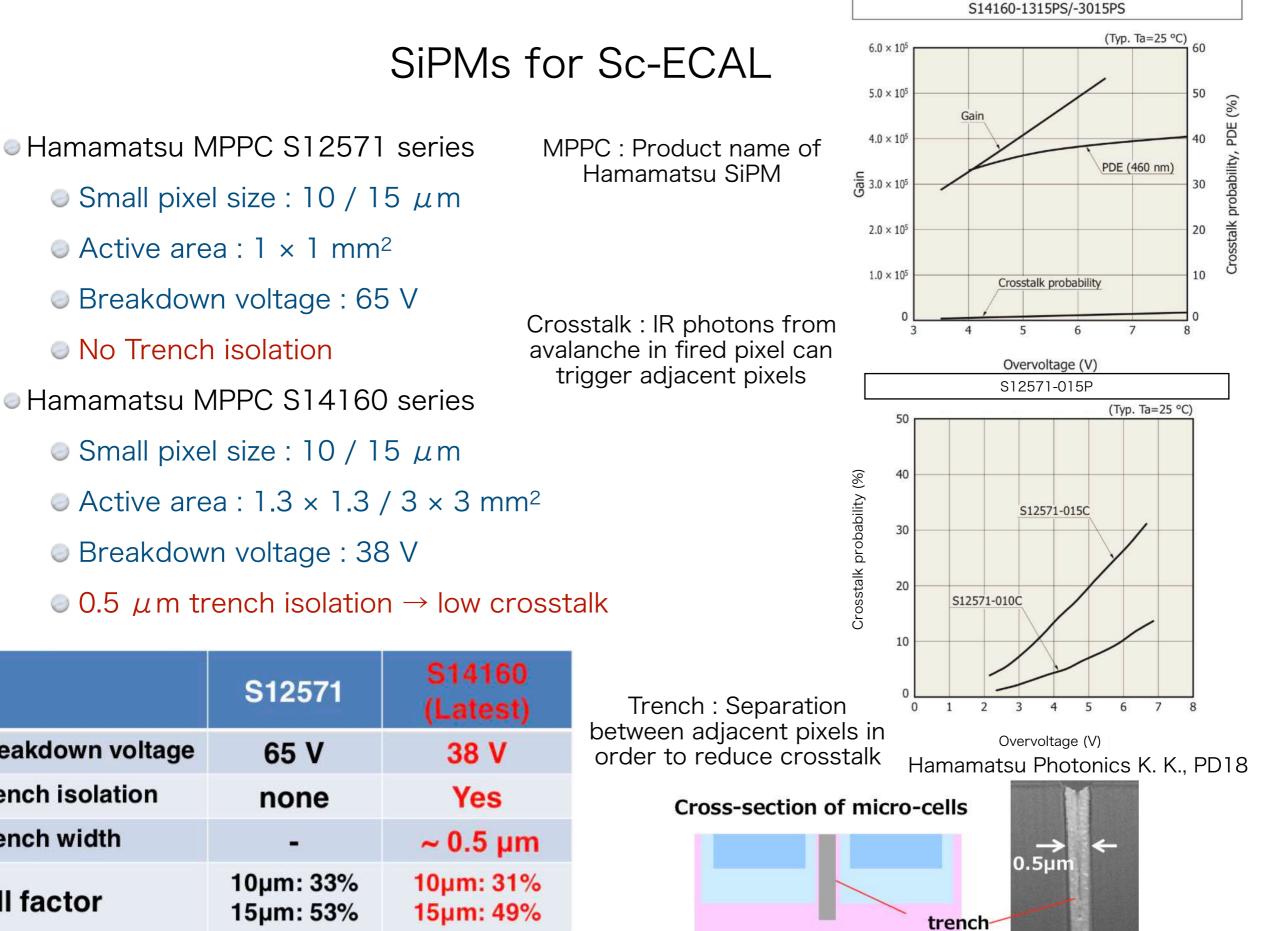
Hamamatsu Photonics K.K., Opto-semiconductor Handbook

Breakdown voltage

Trench isolation

Trench width

Fill factor



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Trench technique of new MPPC

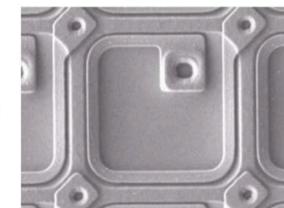
15 µm

10 µm

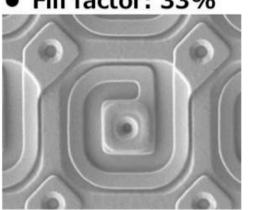
- MPPC S14160 series employ trench technique
 - Low crosstalk
 - Low operation voltage
 - No reduction of fill factor
- Longer tail due to larger cell capacitance
 - Longer recovery time
- Saturation is improved for new MPPC?
 - Low crosstalk \rightarrow saturation \downarrow
 - Longer recovery \rightarrow saturation \uparrow

Old design (w/o trench)

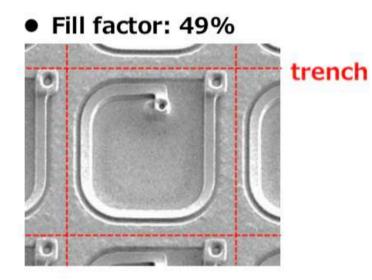
• Fill factor: 53%

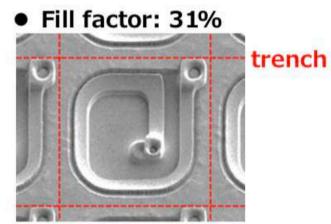




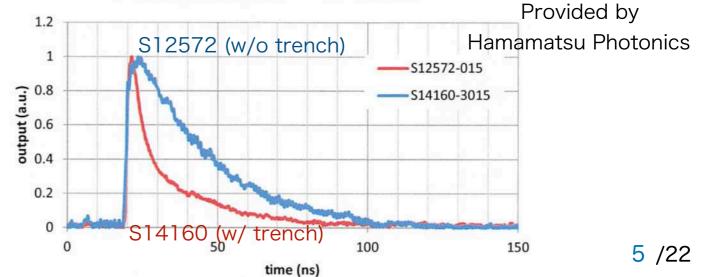


Hamamatsu Photonics K. K., PD18 New design (w/ trench)





S14160-3015 vs. S12572-015



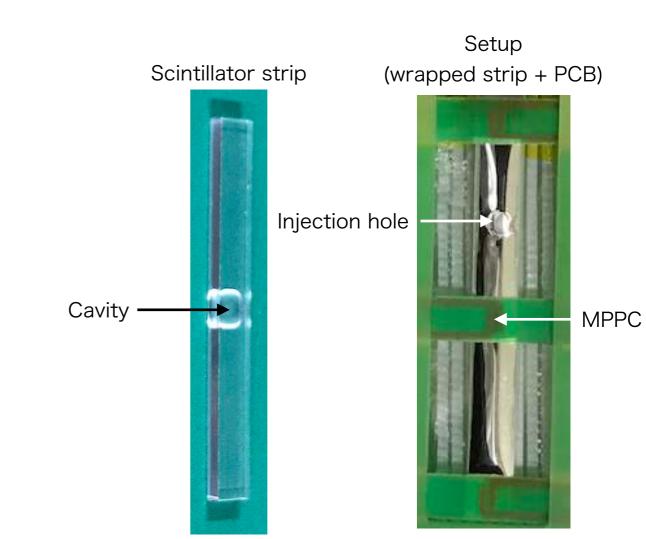
Experimental setup

Laser

- Igo nm laser : Scintillation excitation, invisible to MPPC
- 470 nm laser : No scintillation excitation, directly detected by MPPC
- Setup for Sc-ECAL
 - \odot 5 × 45 × 2 mm³ scintillator strip (EJ-212) with center dimple
 - MPPC w/o trench : S12571-015P
 - Active area : 1.0 × 1.0 mm²
 - Pixel pitch : 15 μ m
 - 4489 pixels

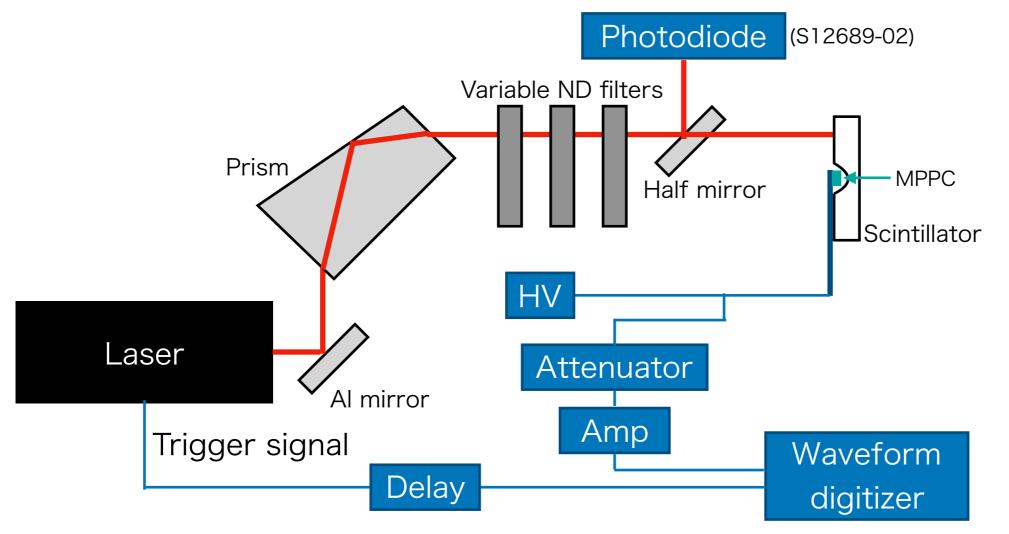
MPPC w/ trench : S14160-1315PS

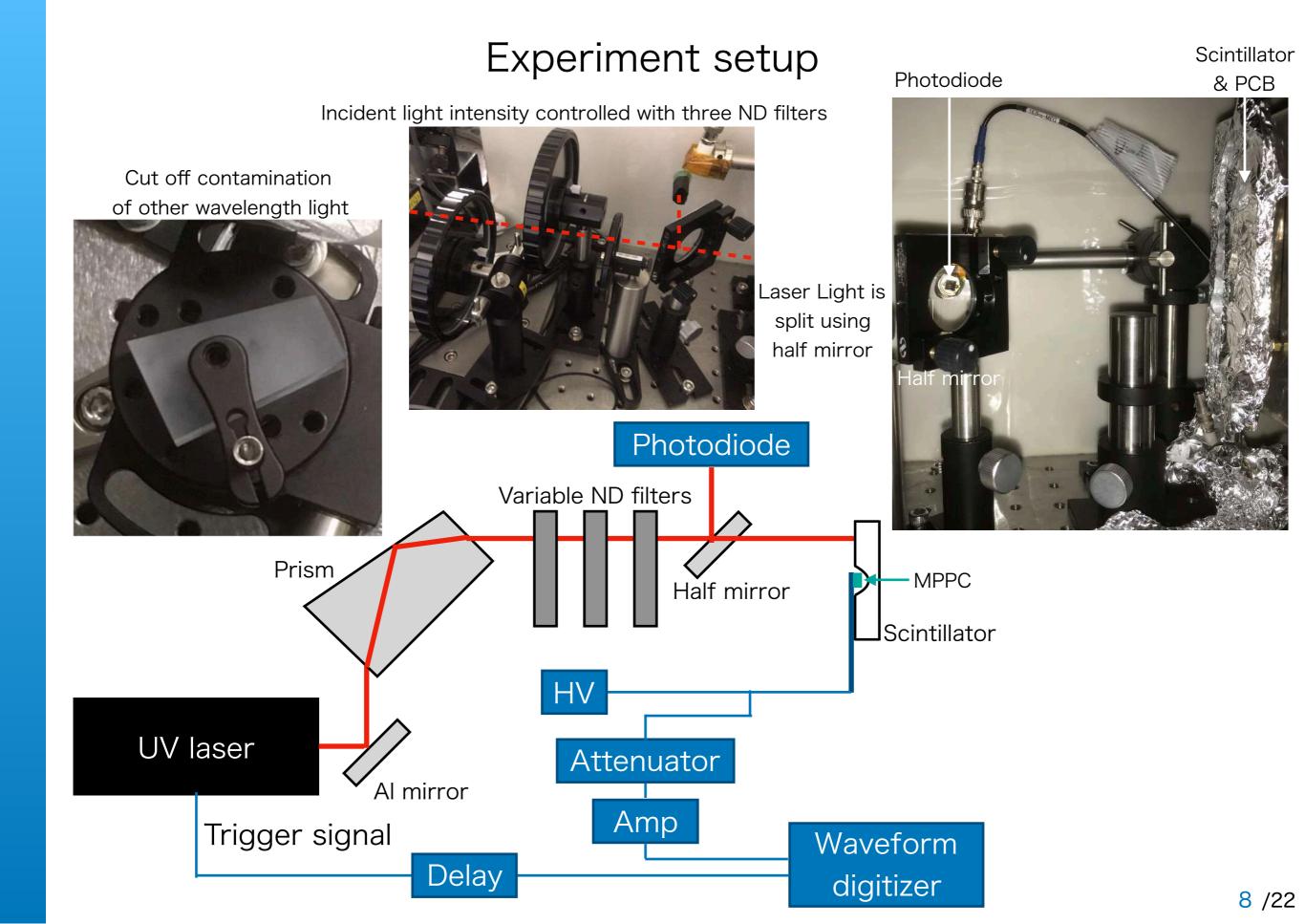
- Active area : 1.3 × 1.3 mm²
- Pixel pitch : 15 μm
- 7296 pixels



Experimental setup

- Excite scintillation light with fast fsec UV pulse laser
 - Laser light is split using half mirror (to scintillator, to photodiode)
 - Incident light intensity is monitored with photodiode
 - MPPC S12571-015P with over voltage of +4 V (Recommended voltage by Hamamatsu)
 - ◎ MPPC S14160-1315PS with over voltage of +4 V (//)
 - Signal attenuations (10 40 dB) used to avoid saturation of electronics

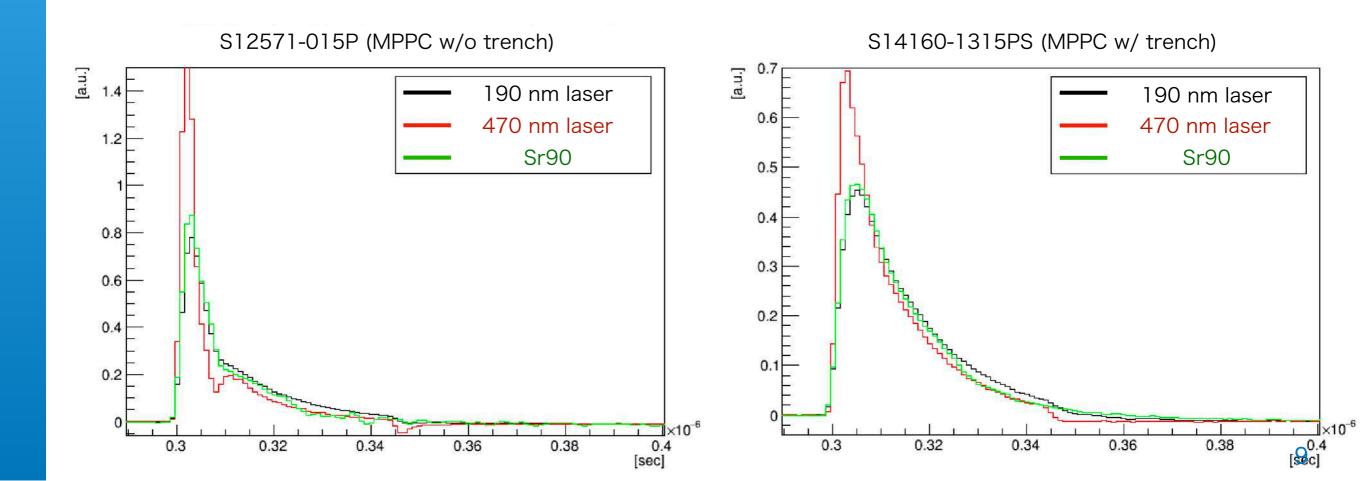




Signal waveform

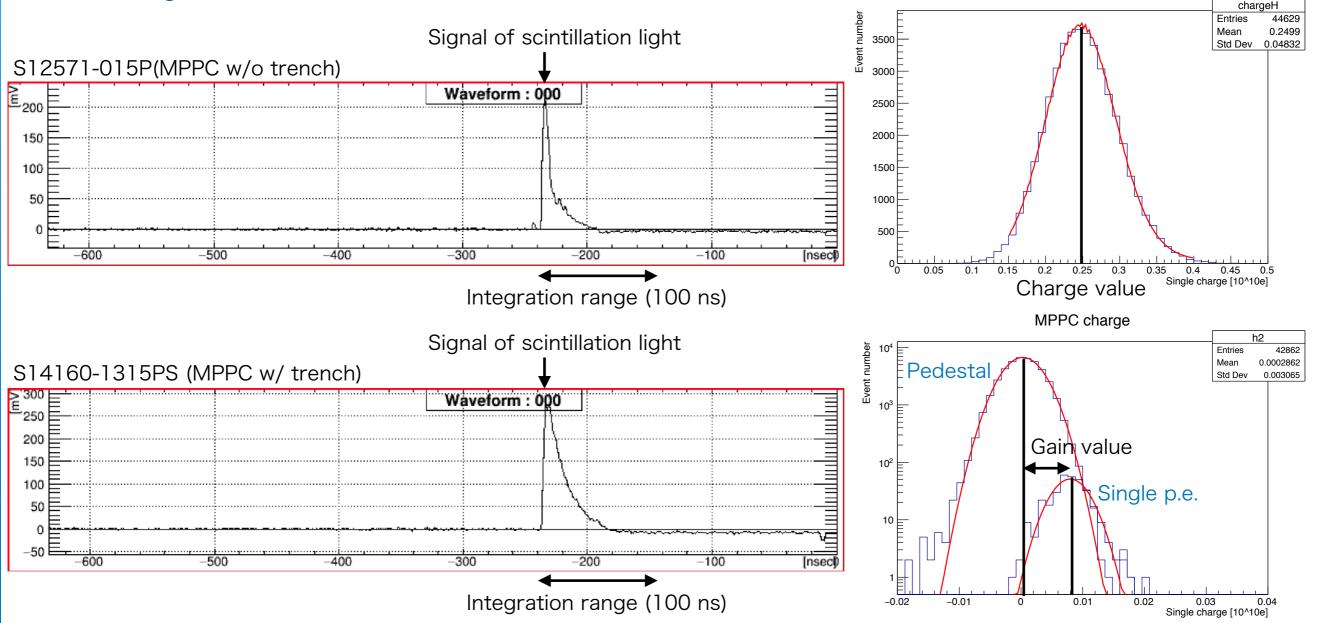
Waveform is compared among 190 nm laser, 470 nm laser, and Sr90

- \bigcirc 190 nm laser, Sr90 \rightarrow MPPC detects scintillation light
- \bigcirc 470 nm laser \rightarrow MPPC detects laser light directly
- Almost the same waveform b/w 190 nm and Sr90
- Faster signal for direct injection of 470 nm laser
 - ➡Suggesting that injected UV laser really excites scintillation light !



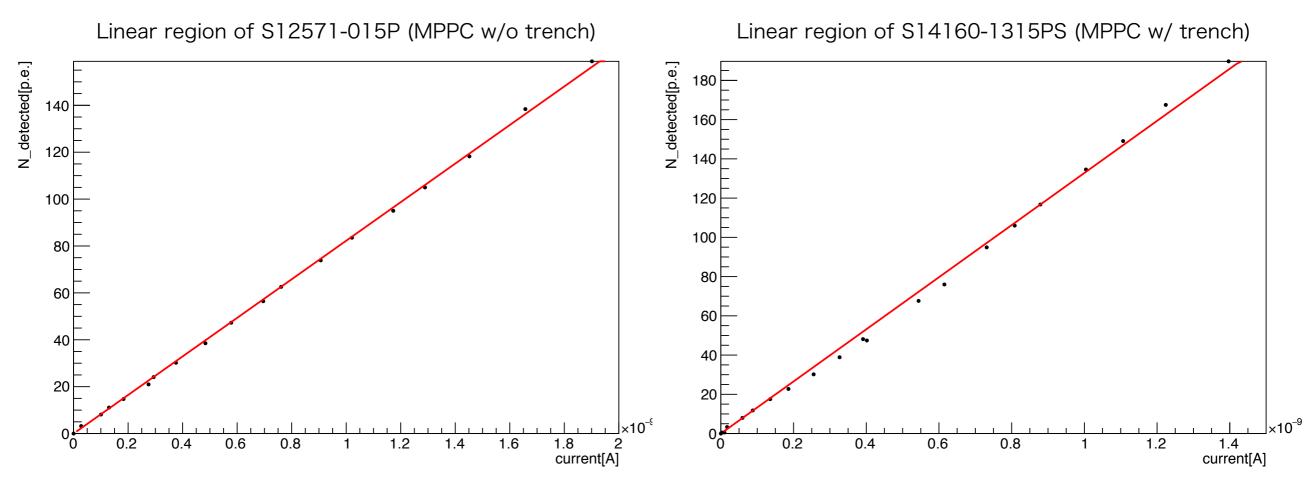
Analysis

- Digitized waveform is integrated to estimate charge.
- The charge is then converted into number of photoelectrons being divided by single photoelectron charge.
 - Single photoelectron charge is obtained from dark noise signal found in off-time region
 MPPC charge



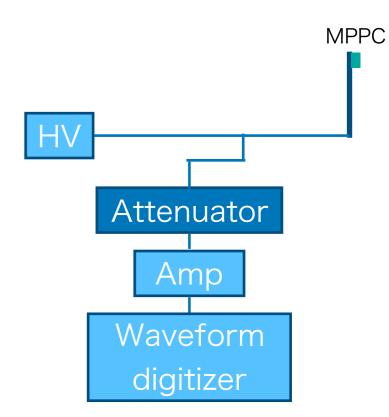
Laser intensity

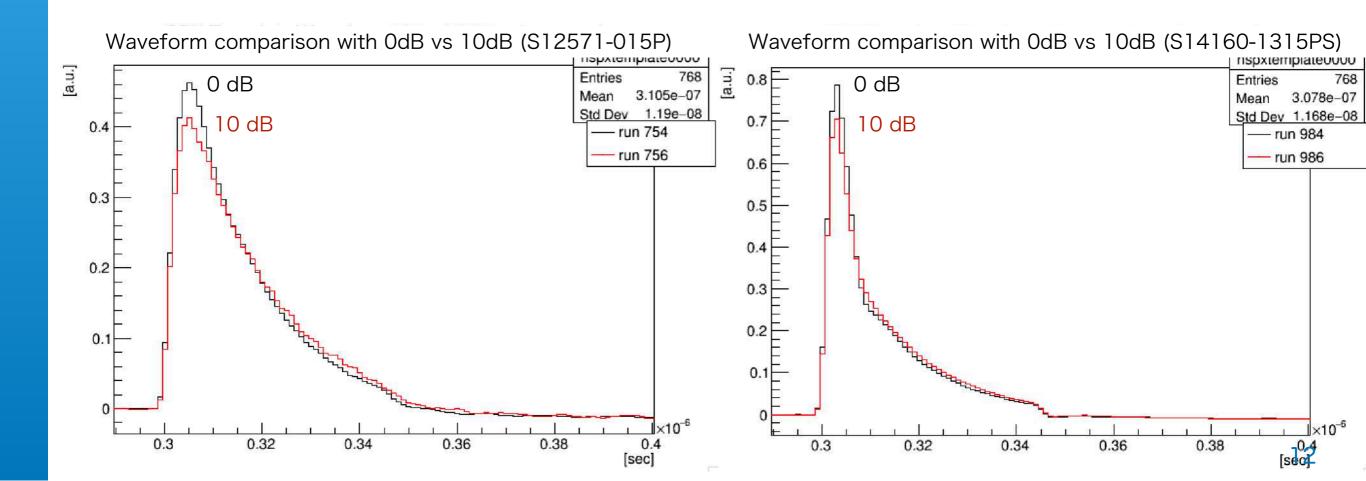
- Incident light intensity is monitored with photodiode
 - Laser light is split using half mirror
- Photodiode current is converted to N_{seed} using calibration constant obtained at low light intensity where no saturation is anticipated
 - (N_{seed} : number of photoelectrons when assuming no saturation)
- Effect of crosstalk and after-pulse is not corrected yet



Attenuation factor

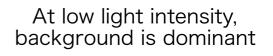
- Oynamic range of DAQ is not sufficient to cover whole light intensity range
 - Need signal attenuation to avoid saturation in electronics
 - 10-40 dB attenuator used
- There is a frequency dependence of attenuator
 - Attenuation rate depends on input pulse shape





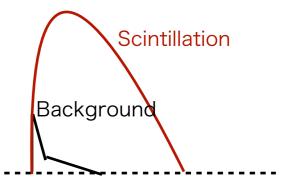
Variation of waveform

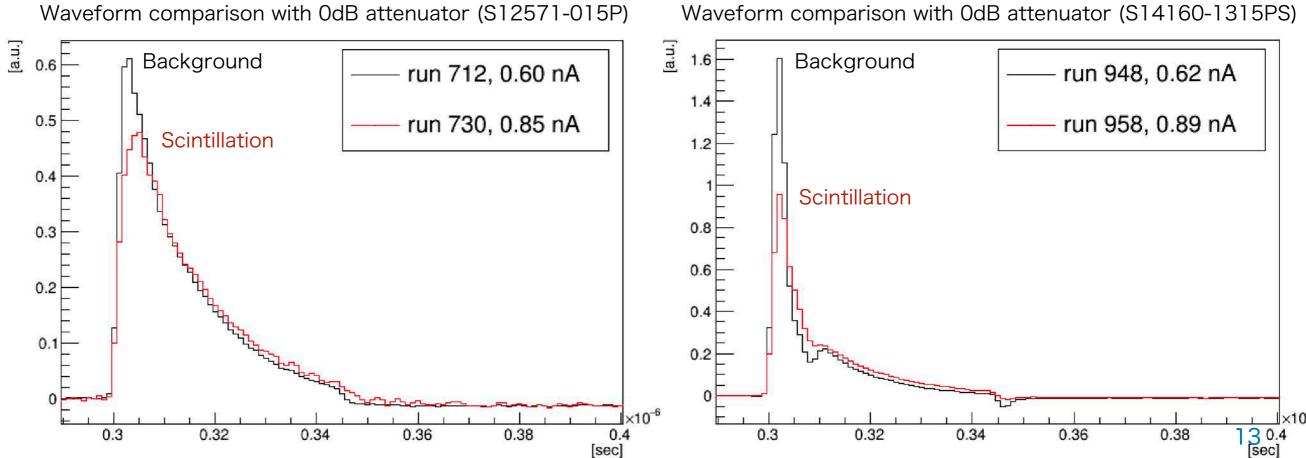
- Variation of waveform depending on light intensity was observed.
- Effect of constant background light at low light intensity
 - Background light comes from optical setup and laser reflection
 - Faster than scintillation light because directly injected to **MPPC**
 - Significant contribution from fast component of background at low light intensity





At higher light intensity, background is negligible





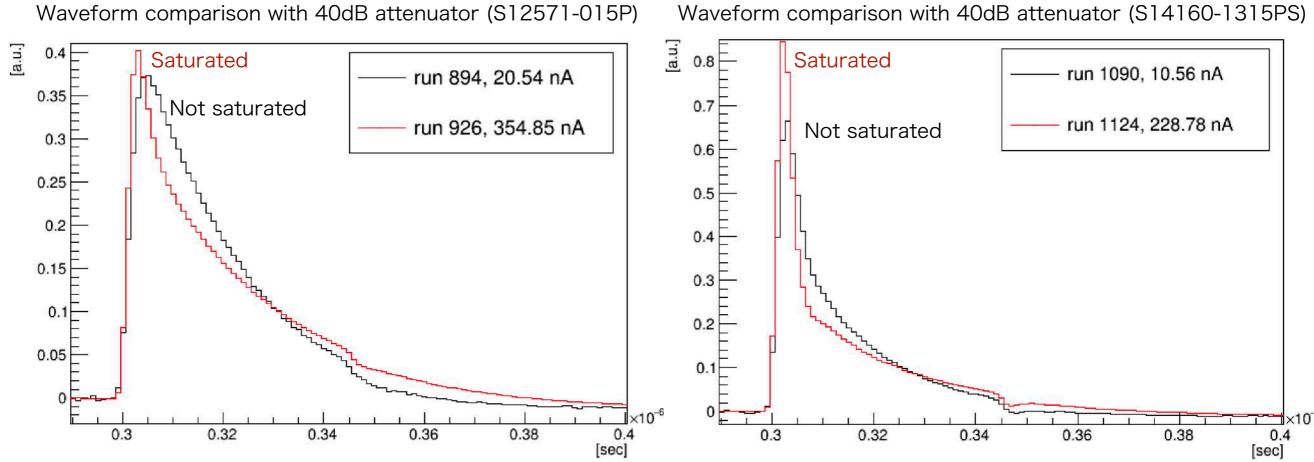
Waveform comparison with 0dB attenuator (S12571-015P)

Variation of waveform

Effect of SiPM saturation at high light intensity

- Saturation deforms waveform at very high light intensity
- These effects change the attenuation rate depending on light intensity



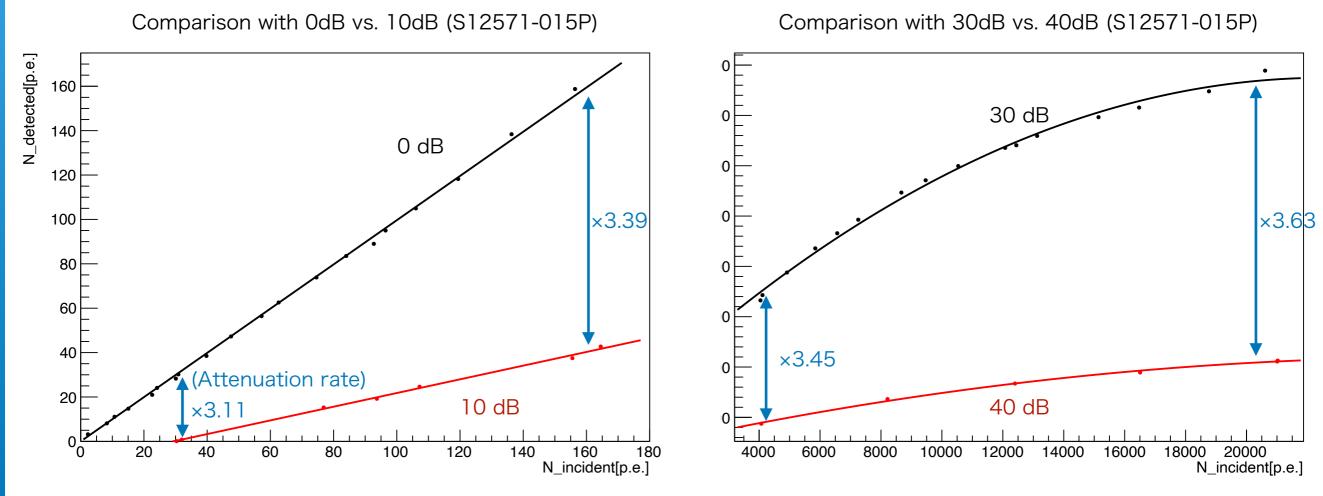


Waveform comparison with 40dB attenuator (S14160-1315PS)

Attenuation Calibration

• Attenuation rate is optimized with factor and offset : $N_{opt} = A * N_{pe} + B$

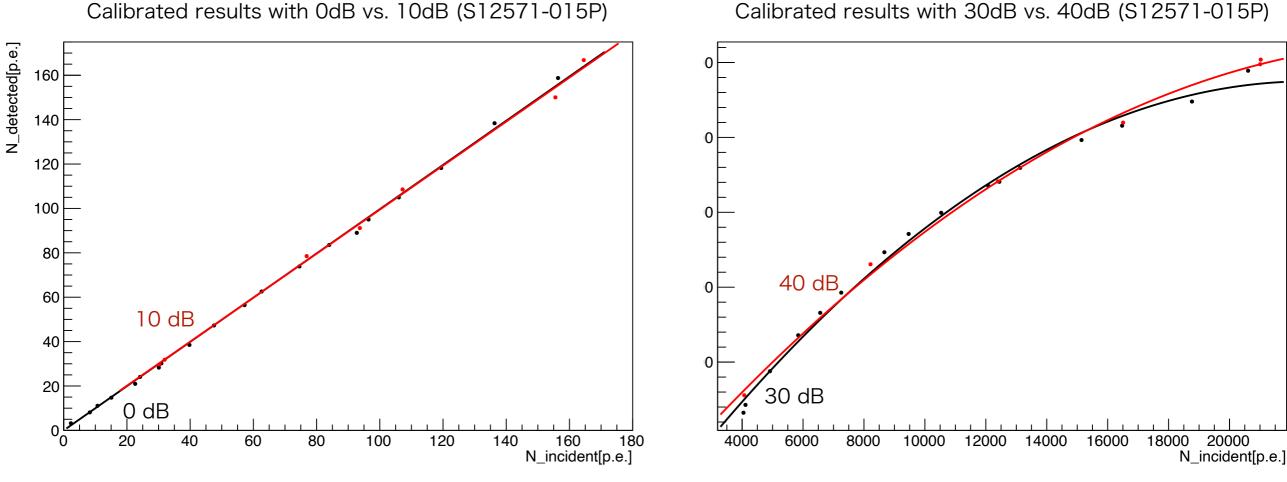
- Fit with linear function and calculate coefficients to match the lines
- Specious factor and offset are used at high light intensity
 - Saturation and waveform variation change the attenuation rate depending on light intensity
 - Fit with polynomial function



Attenuation Calibration

• Attenuation rate is optimized with factor and offset : $N_{opt} = A * N_{pe} + B$

- Fit with linear function and calculate coefficients to match the lines
- Specious factor and offset are used at high light intensity
 - Saturation and waveform variation change the attenuation rate depending on light intensity
 - Fit with polynomial function



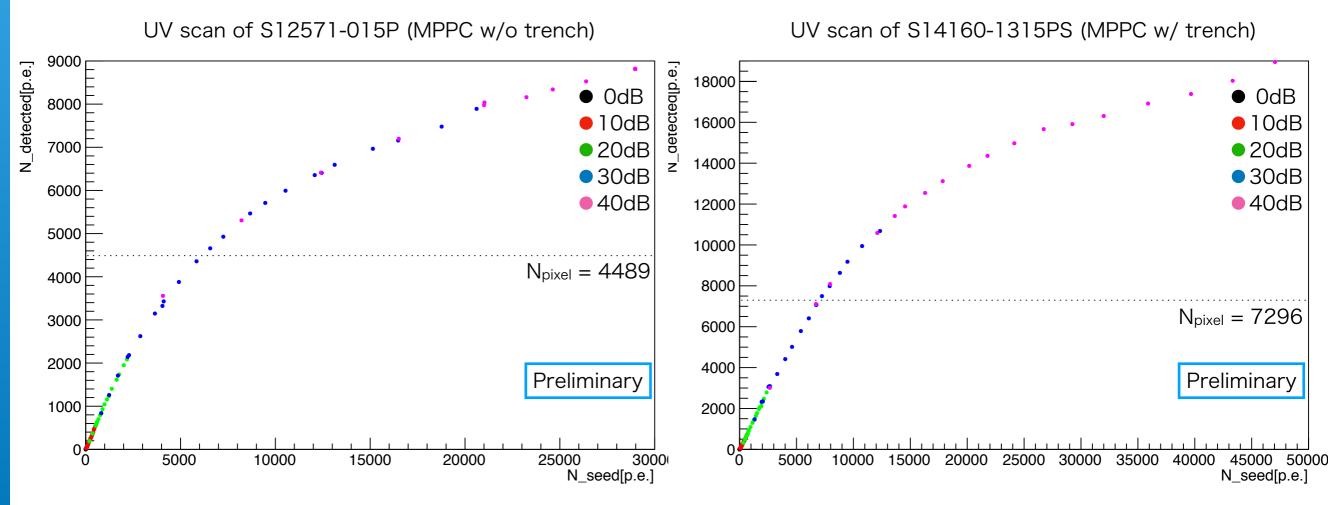
Calibrated results with 30dB vs. 40dB (S12571-015P)

Saturation curve with 190 nm laser

Over-saturation is observed for both MPPCs

N.B. still some uncertainties in estimation for signal attenuation factors

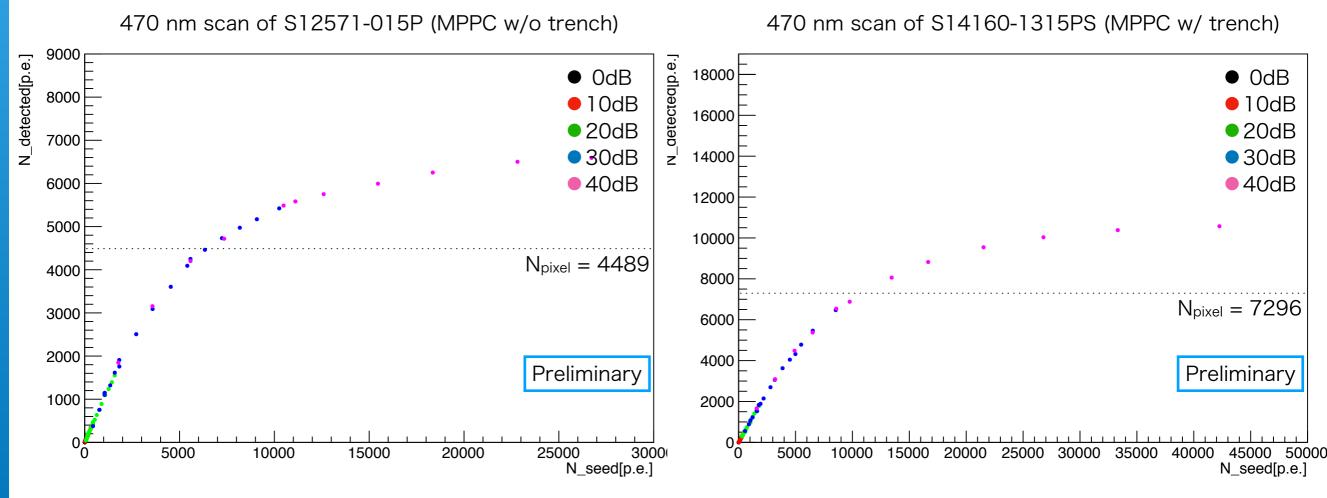
- We observed that the attenuation factor depends on light intensity
- Probably due to change in signal shape caused by MPPC saturation



Saturation curve with 470 nm laser

- Saturation curve using 470 nm laser is measured to compare with 190 nm laser
- Stronger saturation compared to 190 nm laser is observed
- Over-saturation is still observed for both MPPCs
 - Due to after pulse and delayed crosstalk?

N.B. still some uncertainties in estimation for signal attenuation factors

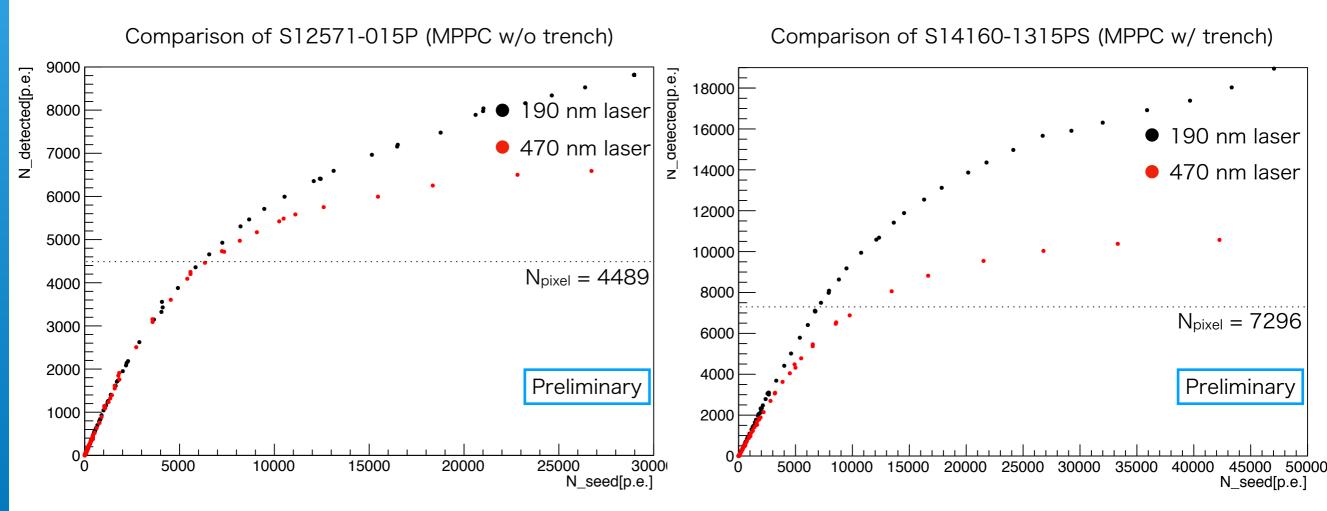


Comparison of 190 nm and 470 nm laser

Significant difference between saturation curves with 190 nm and 470 nm laser

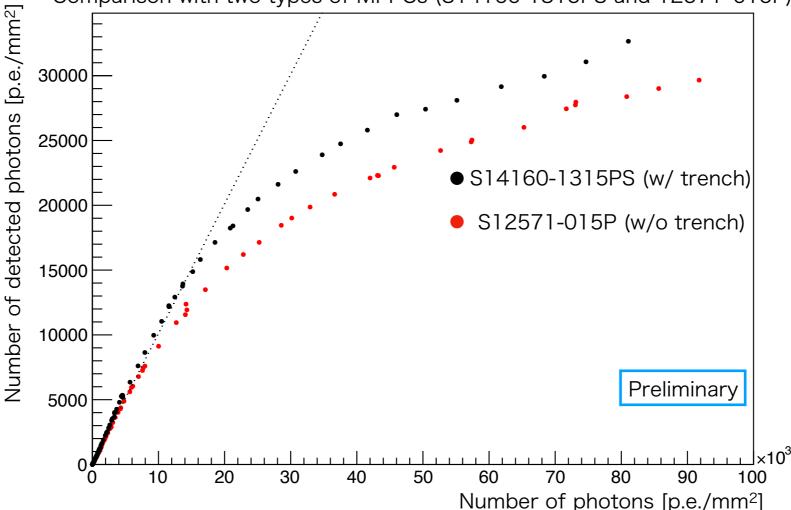
The effect of time constant of scintillation light emission is observed

Can be a big impact on saturation correction



Comparison of two MPPCs with 190 nm laser

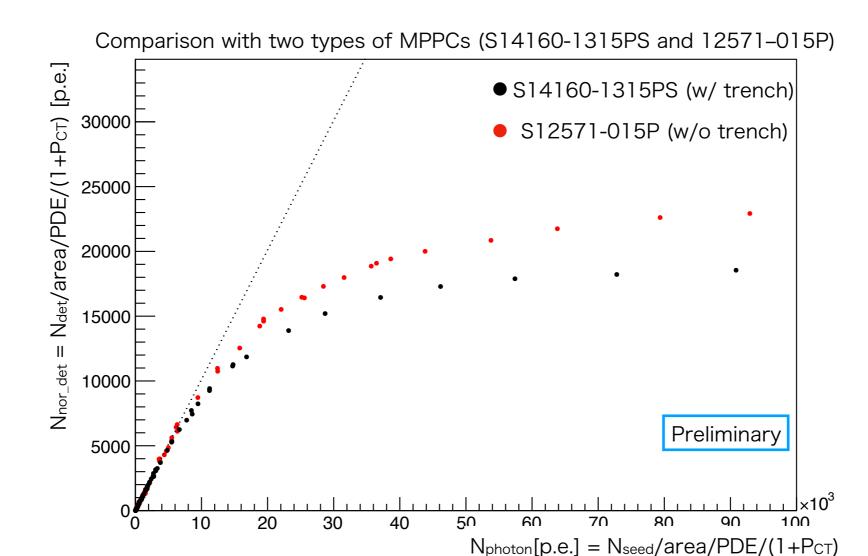
- Normalized by sensor area, PDE and crosstalk probability to compare saturation curves between two MPPCs
- MPPC w/ trench is less saturated compared to MPPC w/o trench
 - Few plots above the linear function (because of wrong attenuation factor?)
- [For S14160-1315PS (w/ trench)] (Lower crosstalk → saturation ↓) > (Longer recovery time → saturation ↑)
 - Effect of longer recovery time is small because of scintillation emission time Comparison with two types of MPPCs (S14160-1315PS and 12571–015P)



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Comparison of two MPPCs with 470 nm laser

- S12571-015P (w/o trench) is less saturated compared to S14160-1315PS (w/ trench)
- [For S14160-1315PS (w/ trench)]
 (Lower crosstalk → saturation ↓) < (Longer recovery time → saturation ↑)
 - Effect of longer recovery time is large because of short duration of laser pulse



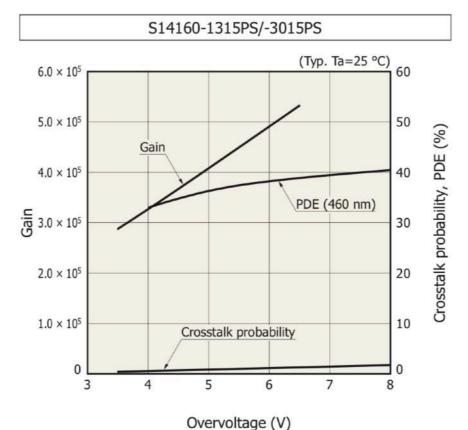
Summary & To do

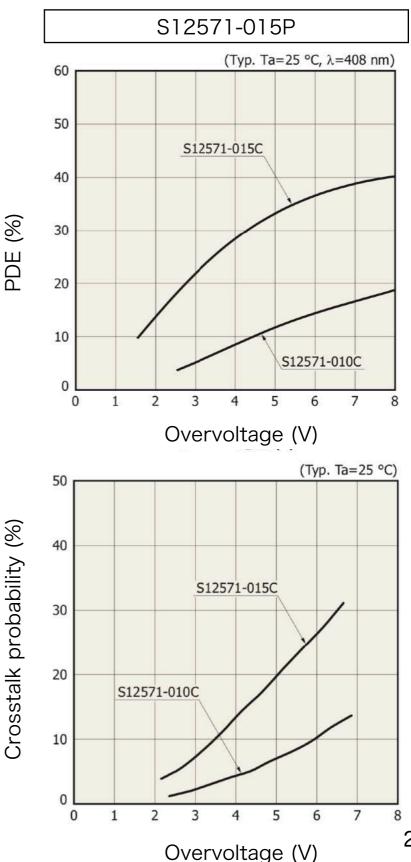
- Saturation curves for MPPCs are measured using scintillation light excited by fast UV-laser with improved setup
- Saturation recovery with scintillation light is observed.
 - It should be taken into account for for saturation correction
 - The measured saturation curves can directly be used for correction
- Saturation curves are measured for two types of MPPCs for Sc-ECAL (w/ and w/o trench)
- The effect of longer recovery time of S14160 (MPPC w/ trench) is found small for scintillation light
 - Longer-tail effect is observed when the measurement of fast pulse
- To do
 - Investigate light intensity dependence of attenuation factor
 - Compare with theoretical model of saturation

Backup

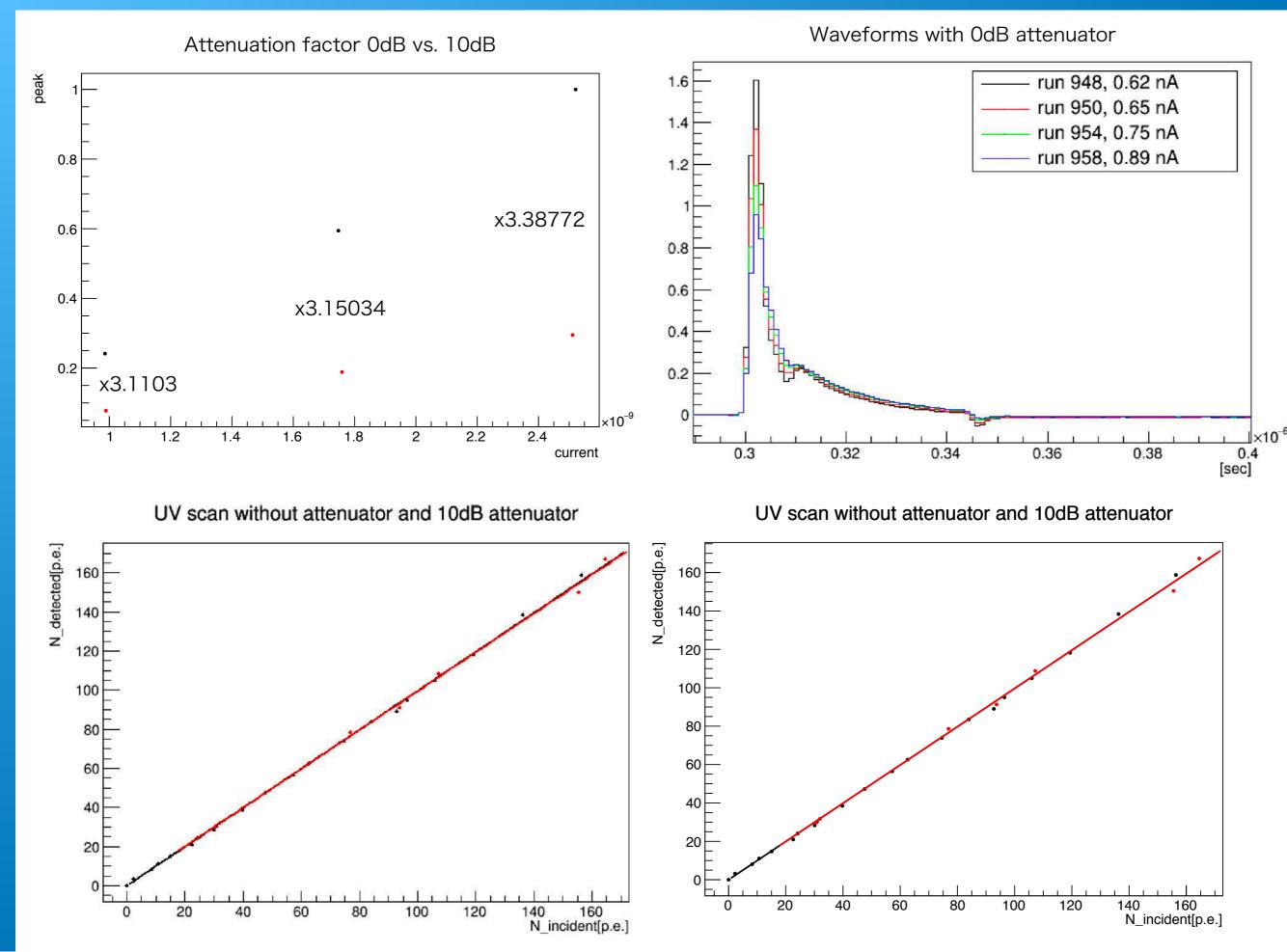
Comparison of two types of MPPCs

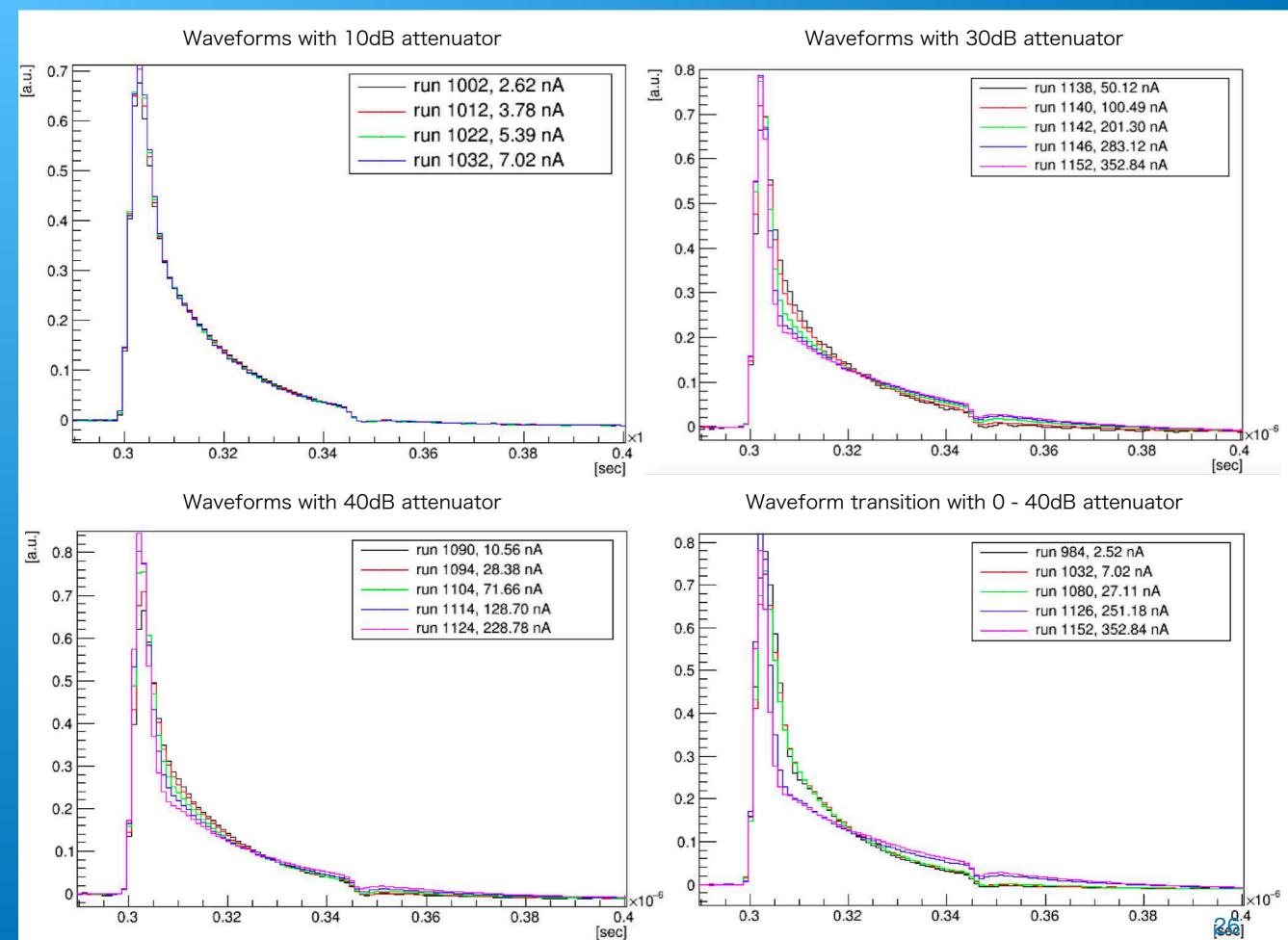
- These plots contain the difference of active area, crosstalk probability and PDE between two types of MPPCs
- Nseed and Ndet are divided by each active area, crosstalk probability, PDE for comparison purpose
 - Nseed is converted into number of inserted photon (Nphoton)
 - Ndet is converted into normalized number of detected photons (Nnor_det)
- Then, we can see directly saturation tendency of each **MPPC**

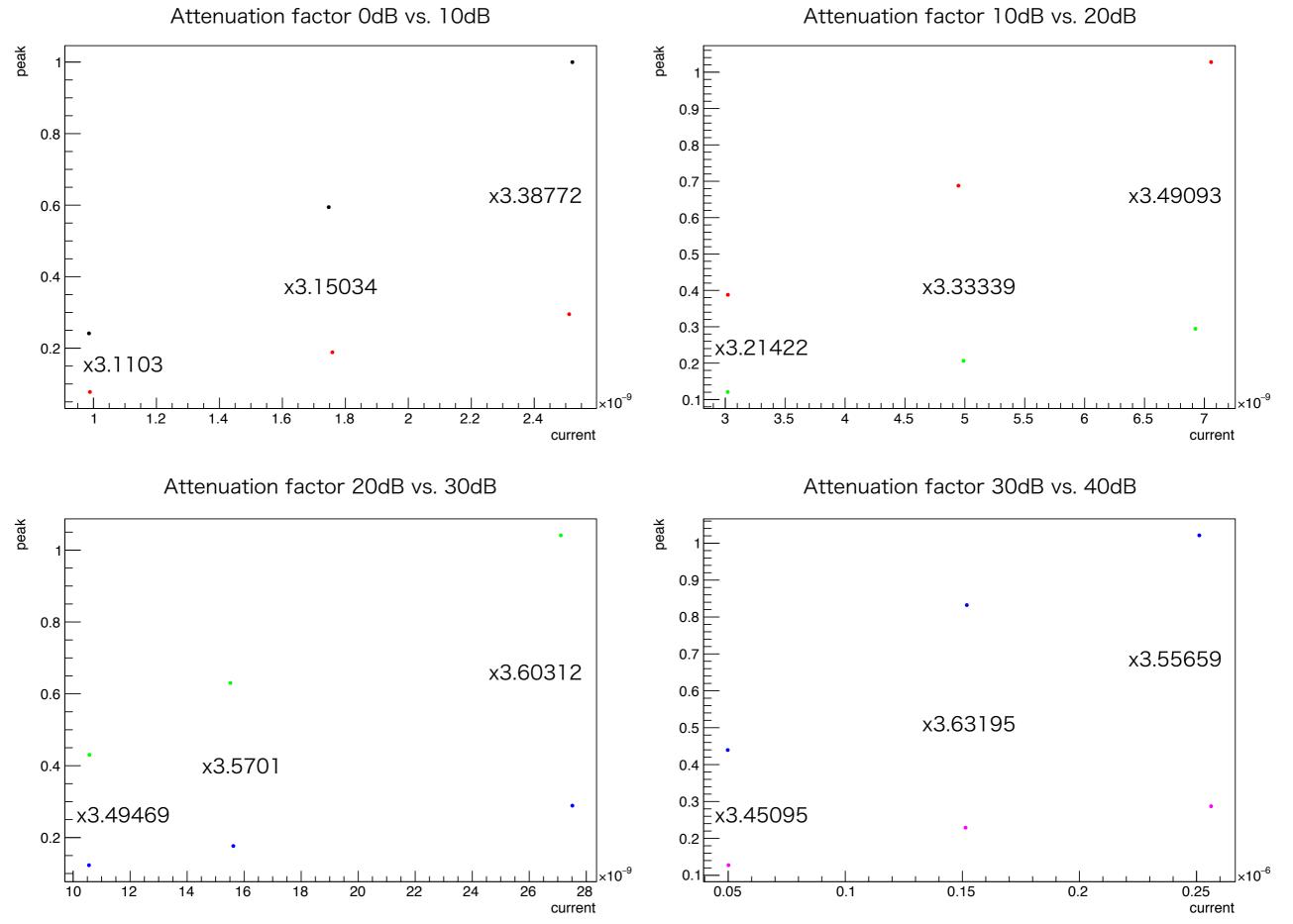




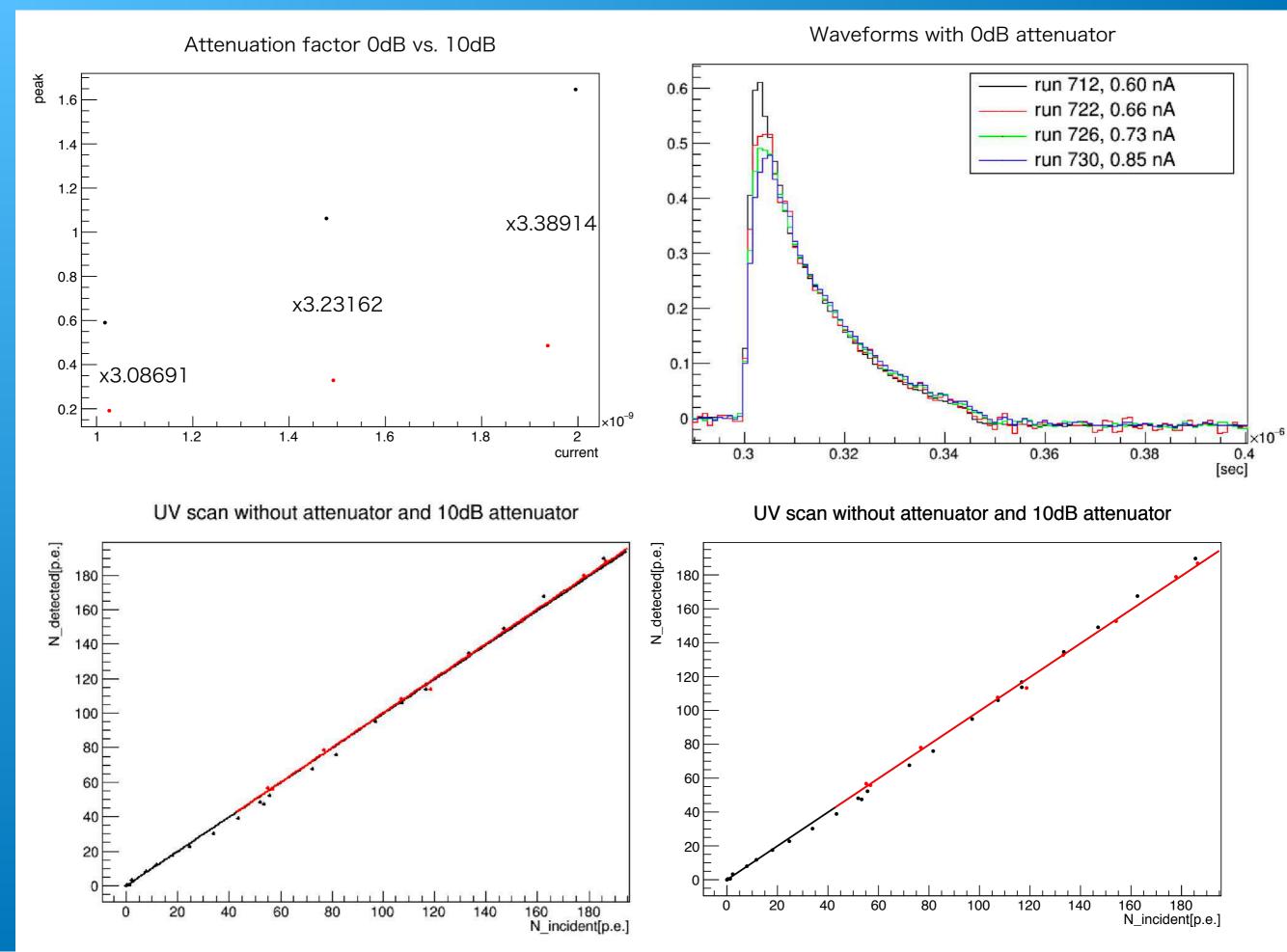
2

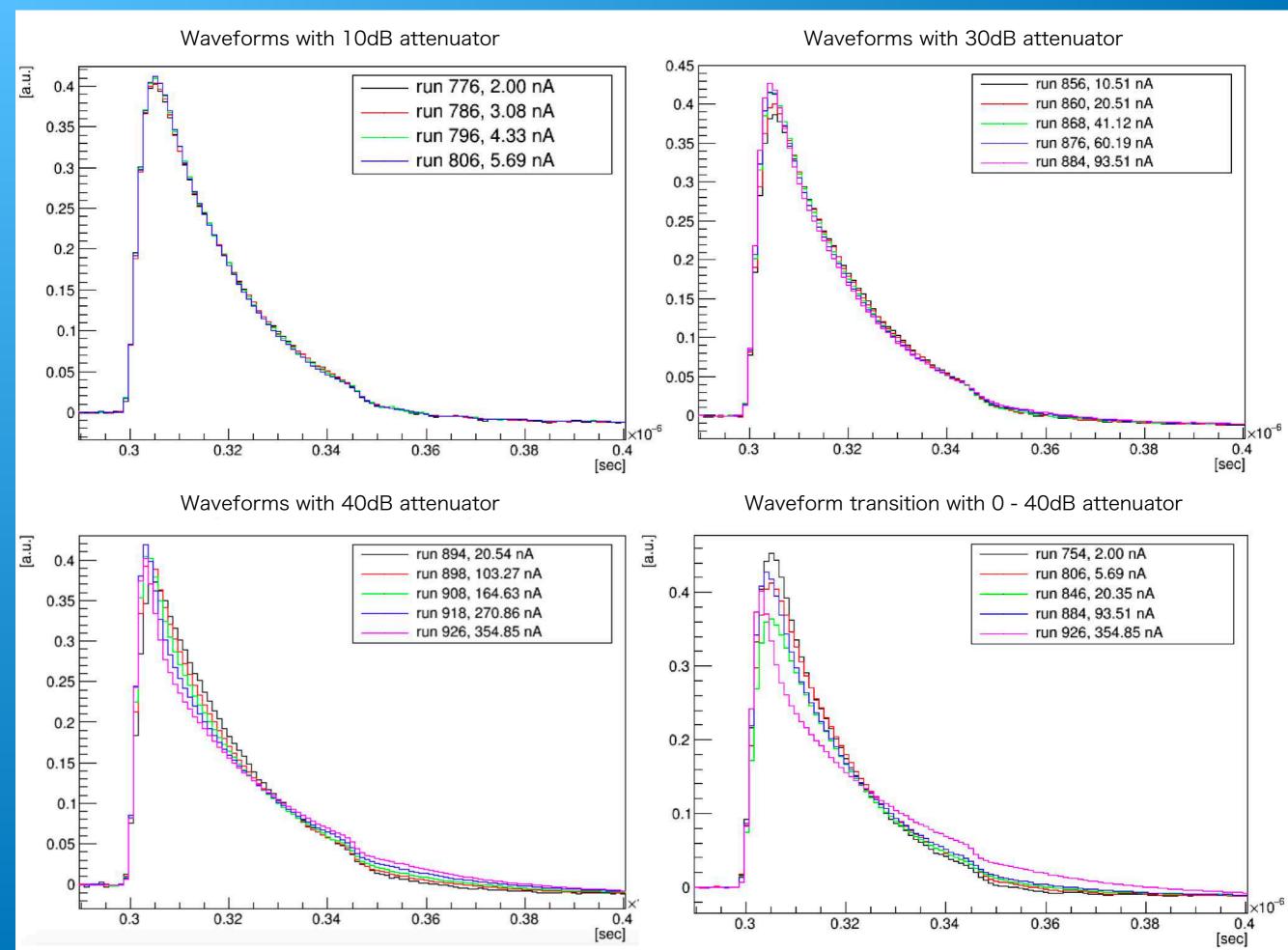


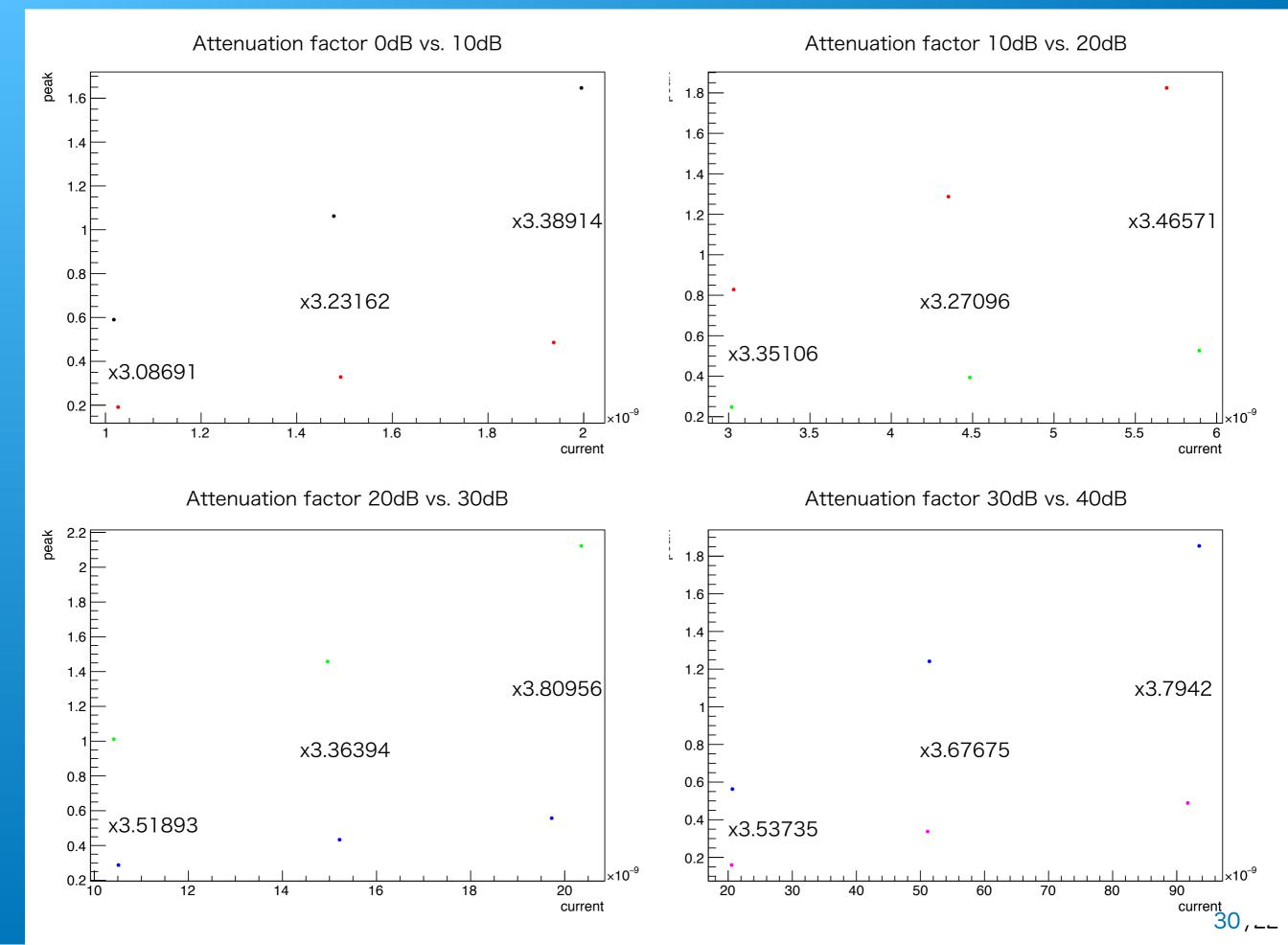




- ' / **- -**



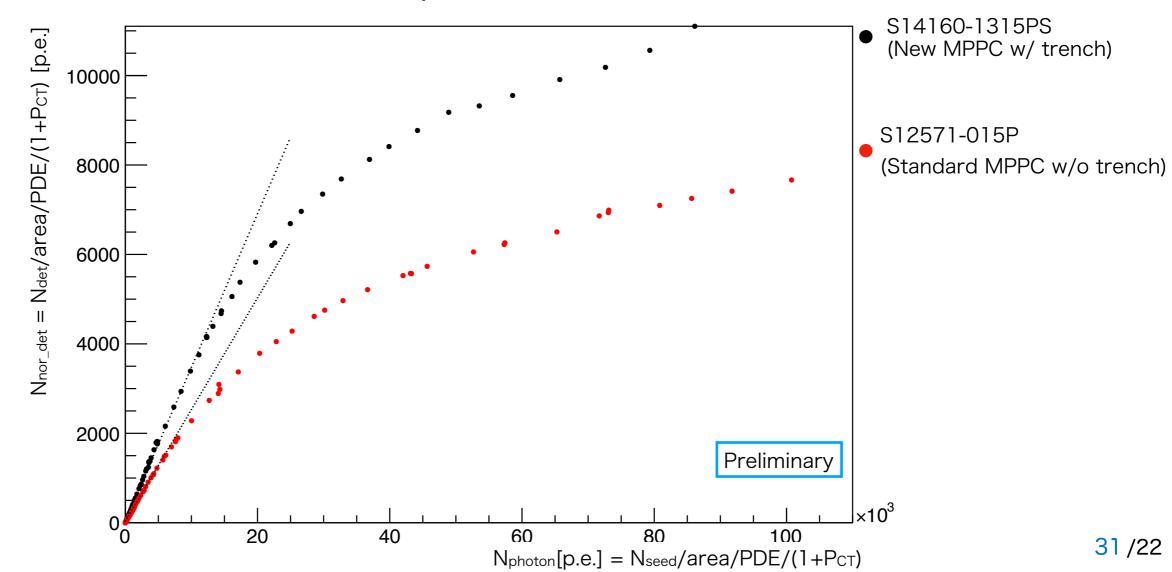




Comparison with two types of MPPCs

The difference of two plots should be consistent with the difference of PDE

- However, S14160-1315PS is less saturated compared with S12571-015P even after correction
- Need further verification
 - We plan to do the same measurement with fast 400 nm laser

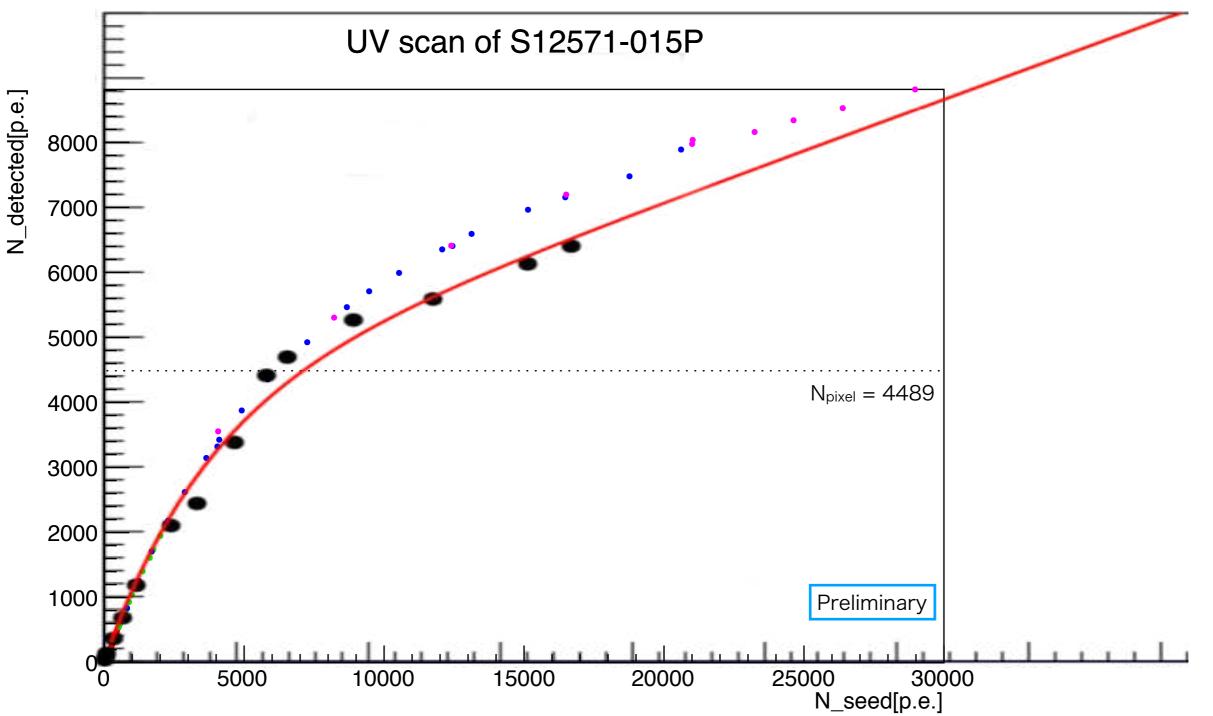


UV comparison of MPPCs

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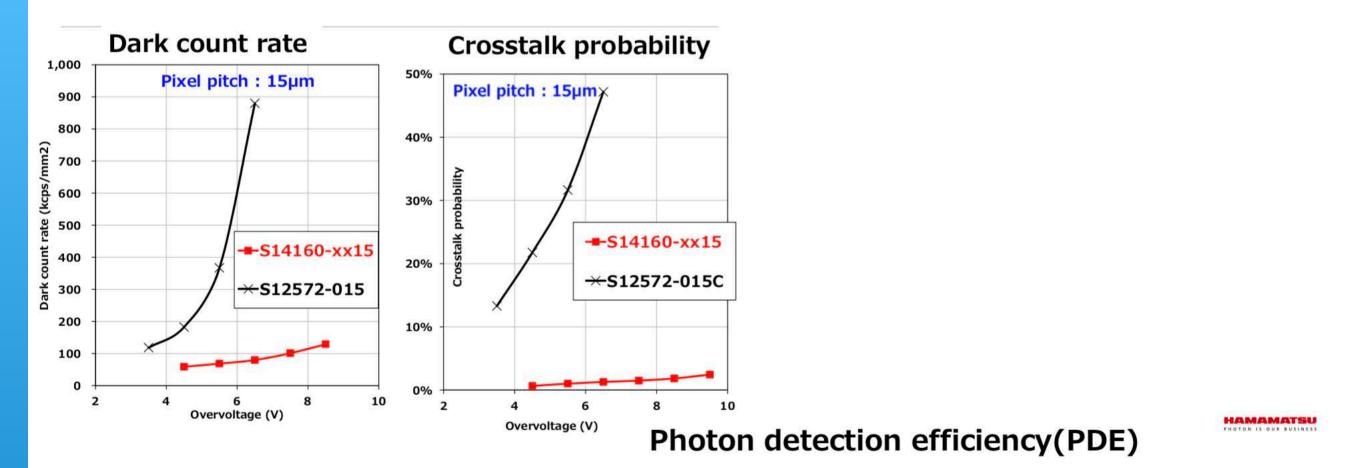
Comparison with previous study

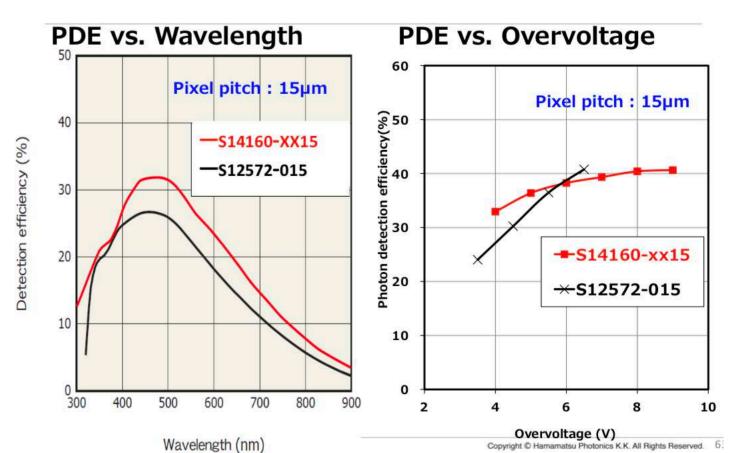
- Comparing the measured saturation of S12571-015P with the previous study where fast laser is directly injected to MPPC
- Saturation recovery observed



HAMAMATSU

Dark count rate & Crosstalk probability

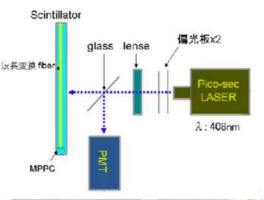


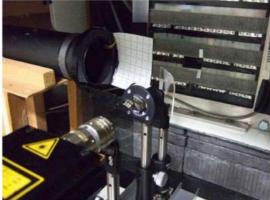


"Study on Saturation of SiPM using UV laser", LCWS2019 at Sendai



- レーザー光をPMTと
 MPPCに分割して測定
- レーザーからの信号の分 割にはガラス板を使用
- この実験ではシンチを通してMPPCに入射





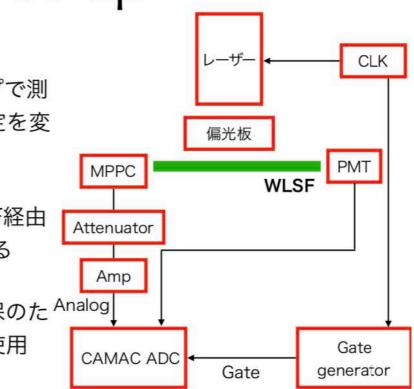
- Set up

 ・ 崔さんのセットアップで測

 定しようとしたが予定を変
- レーザーの光をWLSF経由
 でMPPCとPMTに送る

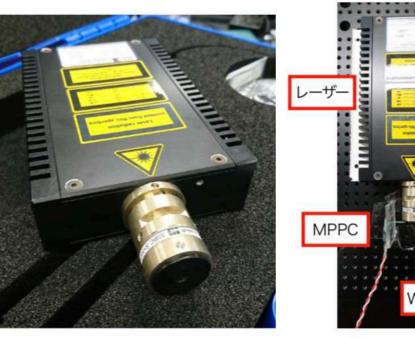
更

MPPCのレンジの確保のた Analog
 め、アッテネータを使用



Laser

- ・ Picosecond Diode Laserを使用
- ・波長: 407nm (measured at 1MHz)
- 光らせるタイミングは内部、あるいは外部 からのCLKで制御
 - 外からの入力の場合は、TTLでもNIM でもいける(TTLが基本らしいが、電圧 のレベルは外から制御可能)
 - ・このCLKはアウトプットも可能
- ・ 強度は0~100%まで変更可能
 - ・ 数値が小さくなるほど強くなるらしい



Yoshimura, Shinshu University

- Set up レーザー 偏光板 MPPC MLSF
 - laserからの光をWLSF経由でもPMT で見えることを確認
 - ・偏光板をレーザー、WLSF間に挿入
 - ・偏光板を回して光量を調整

結果

- 12571-015Pを用いて測定
- ・以下の式で近似 $N'_{NLO} = N_{NLO} \times \frac{\beta + 1}{\beta + \epsilon N_{in}/N_{LO}}$ $N_{NLO} = N_{LO} + \alpha N_R$ $= N_{LO} + \alpha (\epsilon N_{in} - N_{LO})$ $N_{LO} = N_{pix} \times (1 - e^{-\epsilon N_{in}/N_{pix}})$
- PMTのレンジを増やす必要があるので、アッ テネータの使用、或いはゲインを下げるこ とでもっと上の領域まで測定したい
- MPPC、PMTとファイバー間の固定がまだ
 不十分なので、この部分の改善の必要あり

